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SHEET 1 OF 1

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(PTO-1449)

U.S. PATENT DOCUMENTS

96/20/05

FOREIGN PATENT DOCUMENTS

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS		CITE NO.	OTHER ART (including Author, Title, Date, Examiner's Initials)
			Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
<i>cp</i>			SCHEUERLEIN, et al. "A 10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in Each Cell" IEEE International Solid-State Circuits Conference (2000) TA 7.2
<i>cp</i>			DURLAM, et al. "Nonvolatile RAM Based on Magnetic Tunnel Junction Elements" IEEE International Solid-State Circuits Conference (2000) TA 7.3
<i>cp</i>			NAJI, et al. "A 256kb 3.0V 1T1MJT Nonvolatile Magnetoresistive RAM" IEEE International Solid-State Circuits Conference (2001) TA 7.8
			DATE CONSIDERED / / 92

Clear *unfair*

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